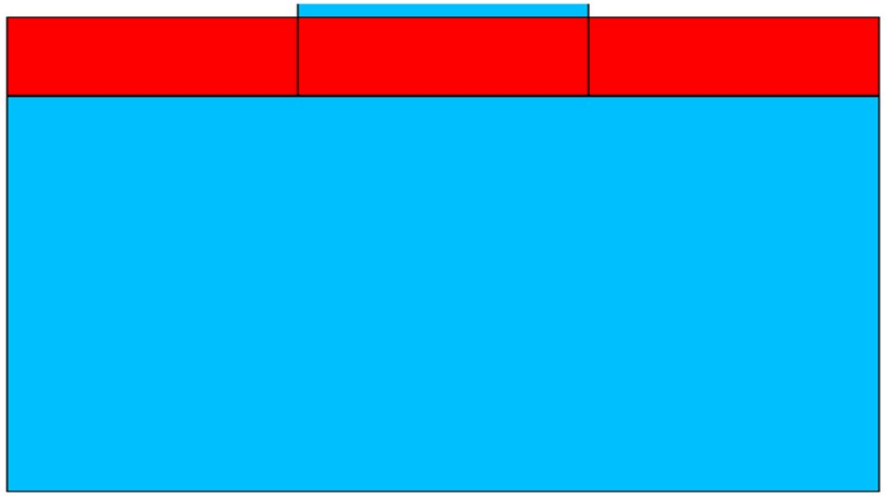


Technology of Next Level
driven through innovation

Monte Carlo
Particle Device Simulator

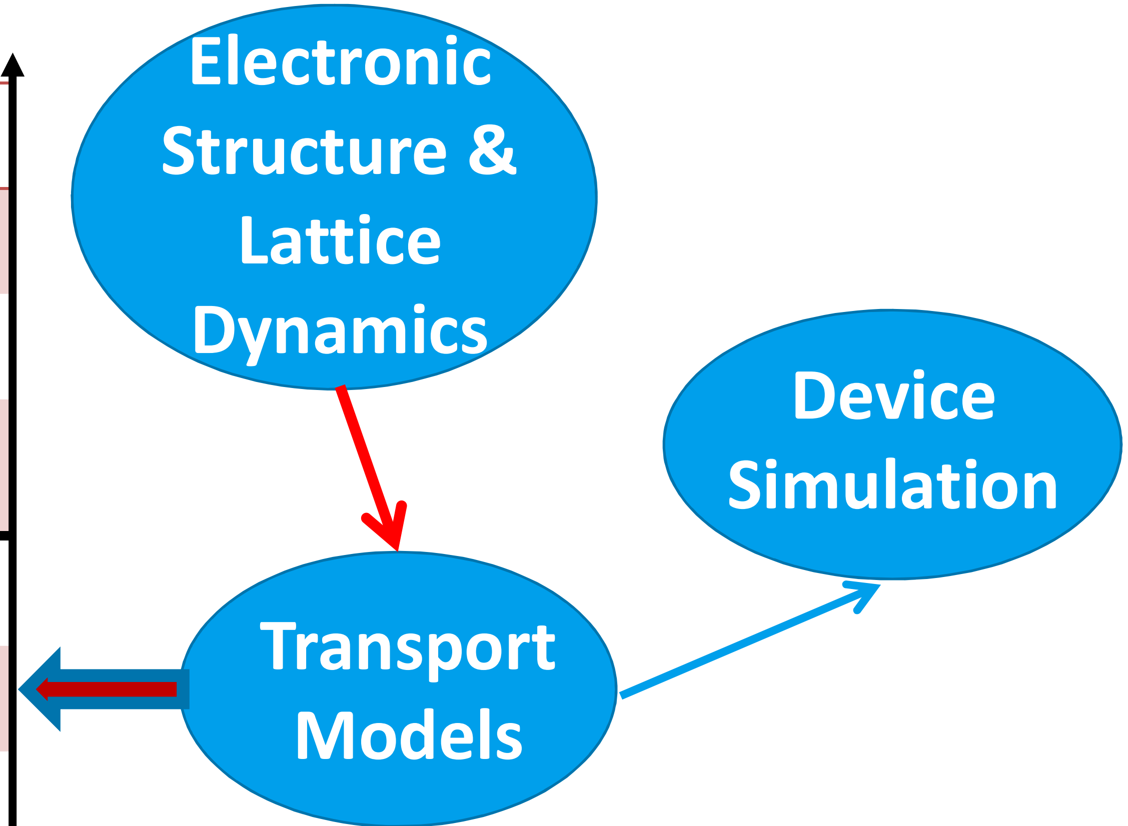
DEVICE MODELING

Approximate — Easy, fast

Semi Classical
- Compact Model
- Drift Diffusion
- Hydrodynamic
- Boltzmann transport (Monte Carlo)

Quantum
- Quantum Hydrodynamics
- Quantum Monte Carlo
- Wigner-Boltzmann
- Green's function method
- Direct solution of Schrodinger

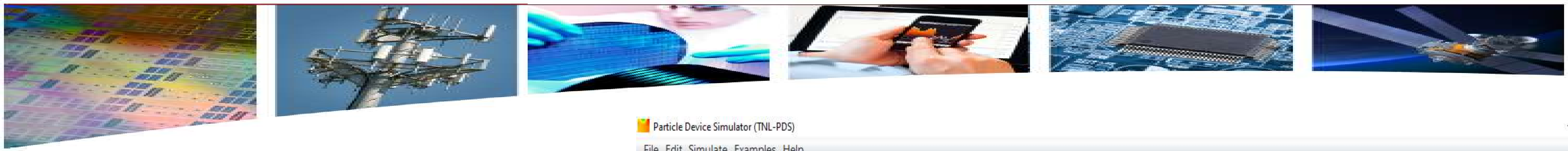
Exact — Difficult



PARTICLE DEVICE SIMULATOR

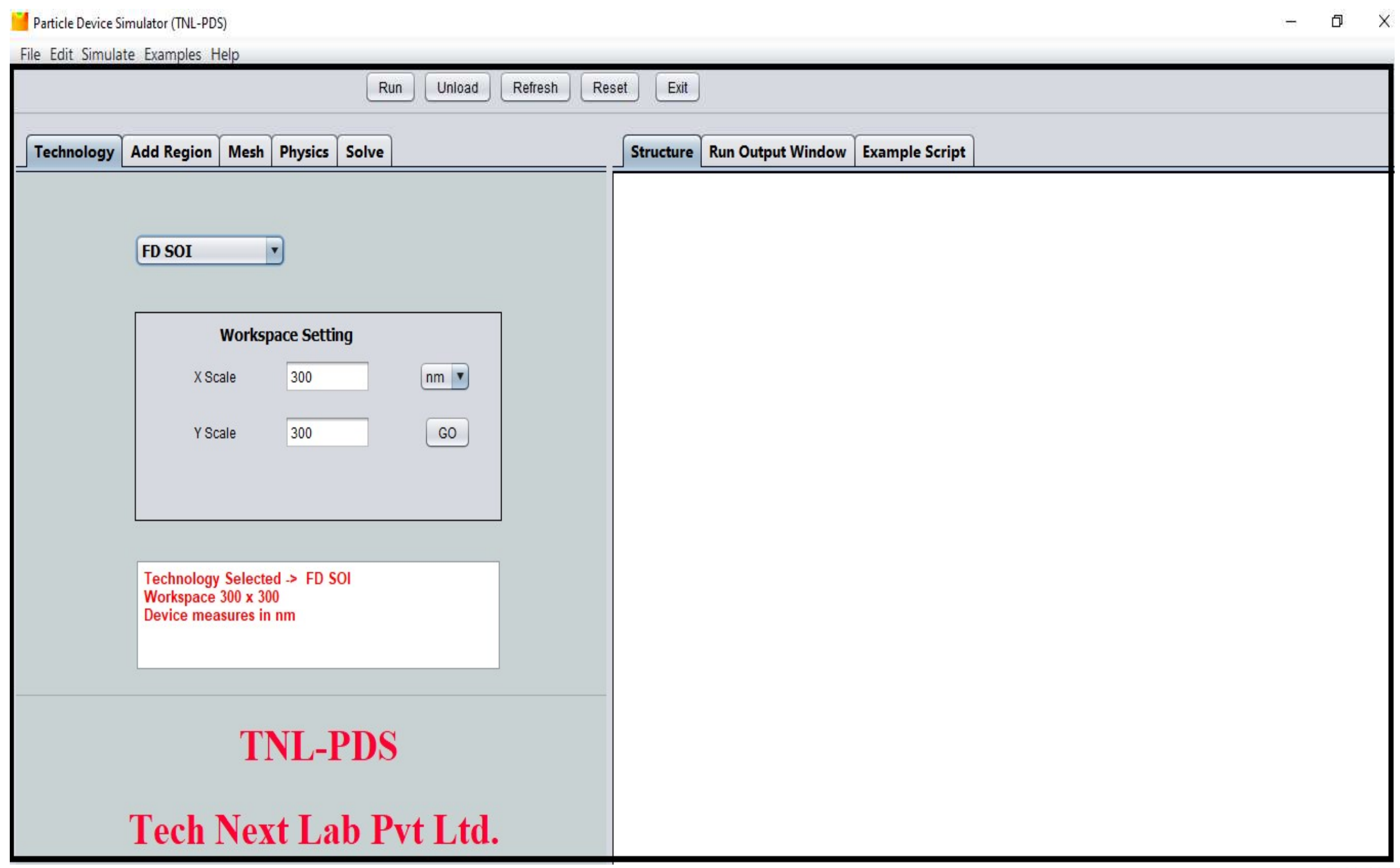
- Particle device simulator takes into account the transport of Monte Carlo particles (Super particles).
- Under influence of applied field, determined self-consistently through the solution of decoupled Poisson's and BTE equation over a suitably small time-step.
- The time step is taken typically less than the inverse plasma frequency obtained with the highest carrier density in the device.

PARTICLE DEVICE SIMULATOR



Technologies implemented in Monte Carlo Particle Device Simulator:

- **MOSFET**
- **FDSOI**
- **Tunneling FET**
- **MESFET**
- **HEMT**



PARTICLE DEVICE SIMULATOR

- Poisson's solution generated over the node points of the mesh,
- Carrier transport solution is obtained using Ensemble Monte Carlo (EMC) on the full range of space coordinates in accordance with the particle distribution itself.
- Particle-mesh (PM) coupling scheme is used for assignment of carrier charge on different nodes and for calculation force on each charges.

SOLUTION

- The classification of Particle-mesh (PM) coupling scheme is included as;
  - ➢ Carrier charge assign at mesh nodes Charge in Cloud (CIC) scheme,
  - ➢ Solution of Poisson's equation on node points through Successive over Relaxation (SOR) method,
  - ➢ Calculation of the mesh defined electric field components,
  - ➢ Interpolation of forces at the particle positions.

BOUNDARY CONDITIONS

- Particle Device Simulator (PDS) contains consistent boundary conditions with those imposed on the potential on the field.
- The particle boundary conditions contain Neumann (zero electric field in the direction normal to the surface) and Dirichlet (contacts) conditions.
- At Neumann boundary the reflecting boundaries has been taken.

QUANTUM CONFINEMENT EFFECT

- Density-gradient model: implemented dependent on non-local quantities.
- Density gradient model is first-order quantum-correction model describe carrier confinement by locally modifying the electrostatic potential through a correction potential γ.
- The Boltzmann-Wigner transport equation can be derived as

$$\frac{\partial f}{\partial t} + v.\nabla_r f - \frac{q}{\hbar}\sum_{\alpha=0}^{\infty}\frac{(-1)^{2\alpha}}{4^{\alpha}(2n+1)!}\nabla_k^{2n+1}V(r).\nabla_k^{2n+1}f = \left(\frac{\partial f}{\partial t}\right)_{coll}$$

QUANTUM CONFINEMENT EFFECT

- The corrected quantum effect is included as

$$\frac{\partial f}{\partial t} + \frac{\hbar . k}{m^*}\nabla_r f - \frac{1}{\hbar}\nabla_r \left(V(r) - \nabla_r^2 \emptyset\right) \nabla_k f = \left(\frac{\partial f}{\partial t}\right)_{coll}$$

The correction potential term in multidimensional space is

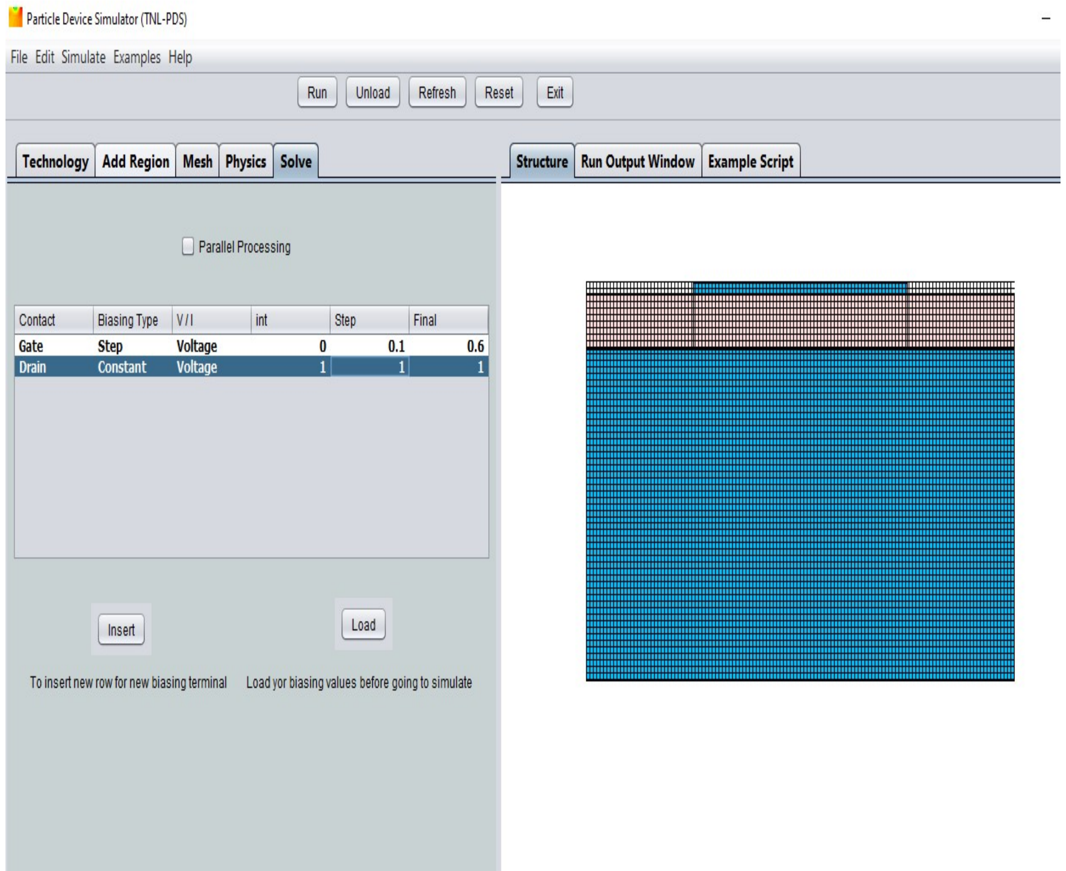
$$\gamma(r,t) = \frac{\hbar^2}{12\lambda k_b T m^*}\left(\nabla_r^2 \emptyset(r,t) - \frac{1}{2k_b T}\left(\nabla_r \emptyset(r,t)\right)^2\right)$$

The fitting parameter λ is determined by comparing the carrier density in a device structure to the carrier density obtained by the solution of Poisson Equation.

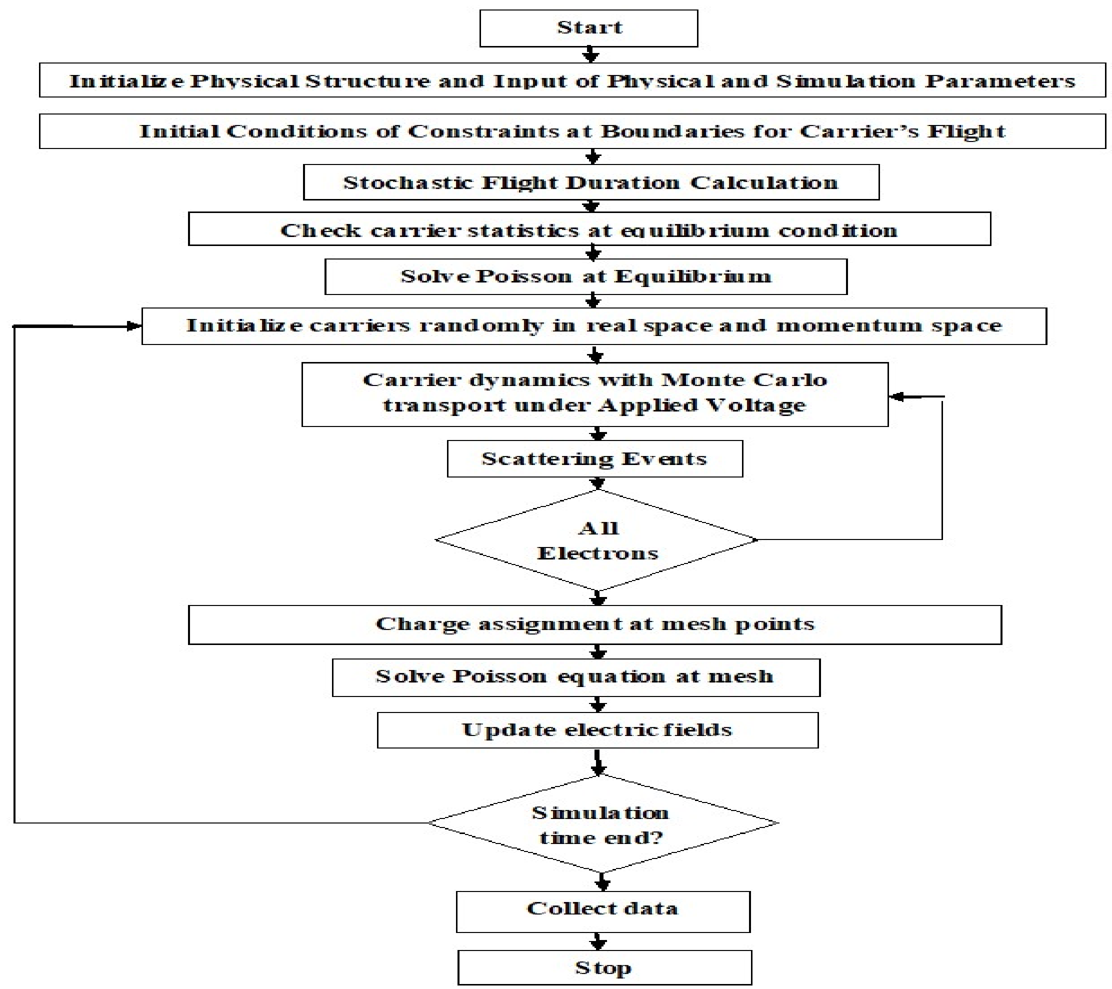
PARTICLE MESH COUPLING

- The particle-mesh method is a widespread model for space charge calculations.
- Particle dynamics under applied electric field requires accurate solution of Poisson’s equation.
- The particle simulation means the assignation of the particle’s charge to the rectangular mesh.
- Two types of the most famous schemes:
  - Nearest Grid Point (NGP)
  - Cloud In Cell (CIC)

FLOW CHART



Flow Chart for program implementation



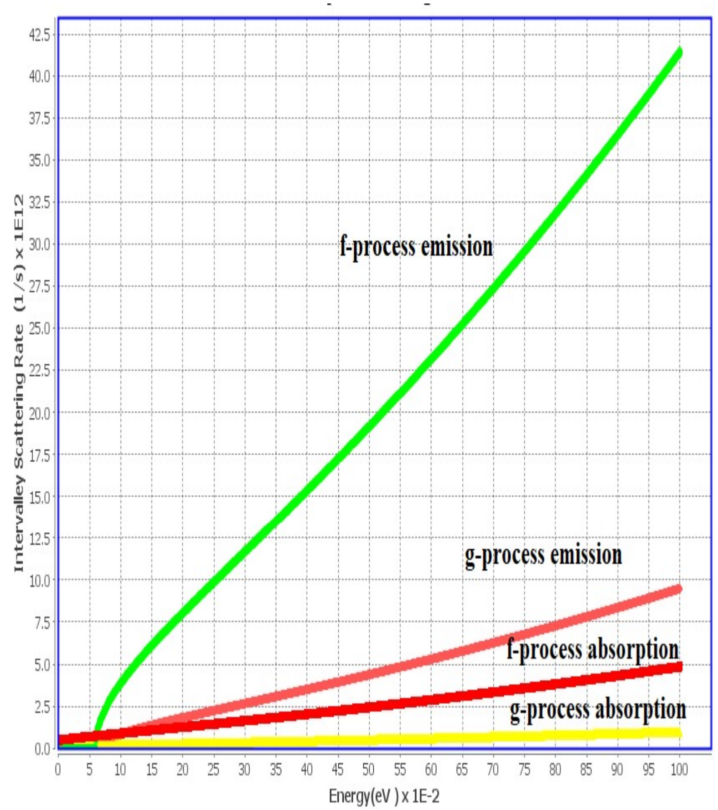
RESULTS

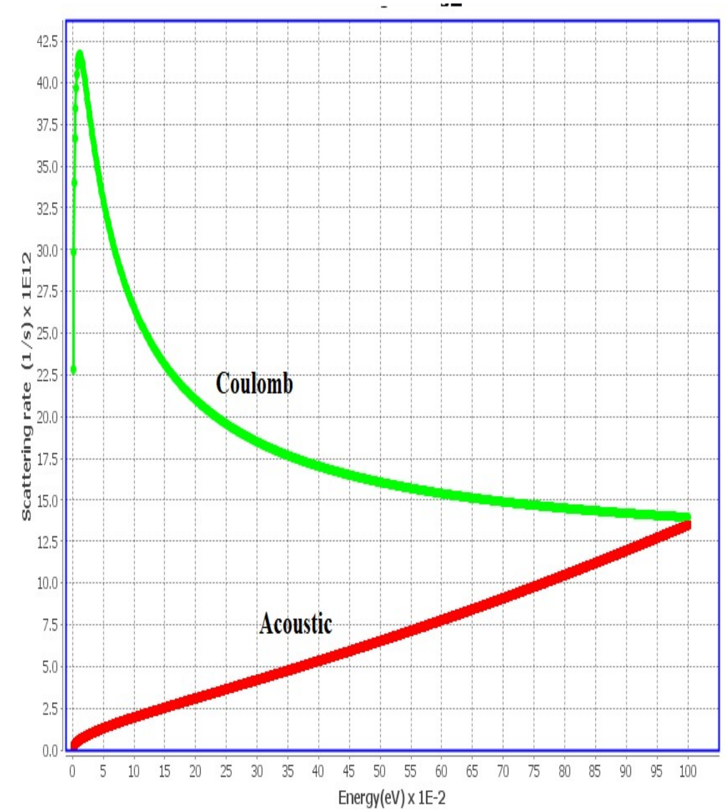
	Nodes (nm)	14nm	10nm	7nm	14nm	10nm	7nm
Structure Parameters		Single Gate			Double Gate		
	L_{eff} (nm)	22	14	10	22	14	10
	W_{eff} (nm)	10		8	10		8
	T_{ox} (nm)	1	0.85	0.75	0.75	0.85	0.75
	Doping (/cm^3)	1×10^{24}	5×10^{24}	2×10^{25}	2×10^{25}	5×10^{24}	2×10^{25}
	T_{SOI} (nm)	40	30	20	20	30	20
Device Parameters	Vth (mV)	0.3	0.22	0.2	0.2	0.4	0.5
	SS (/mV/dec)	63.3	67.9	82.9	82.9	87.4	72.2
	gm (mS/µm)	0.252	0.437	0.499	0.499	0.494	0.449

FDSOI TECHNOLOGY UP TO 7NM

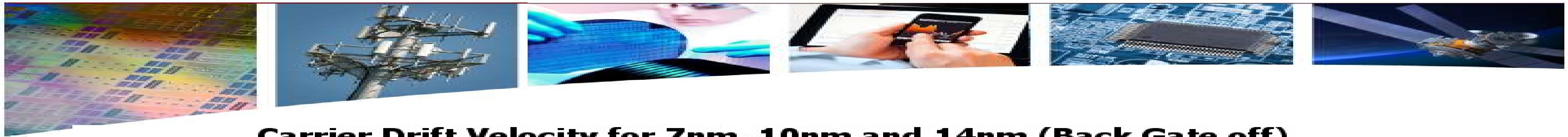
Scattering Rates

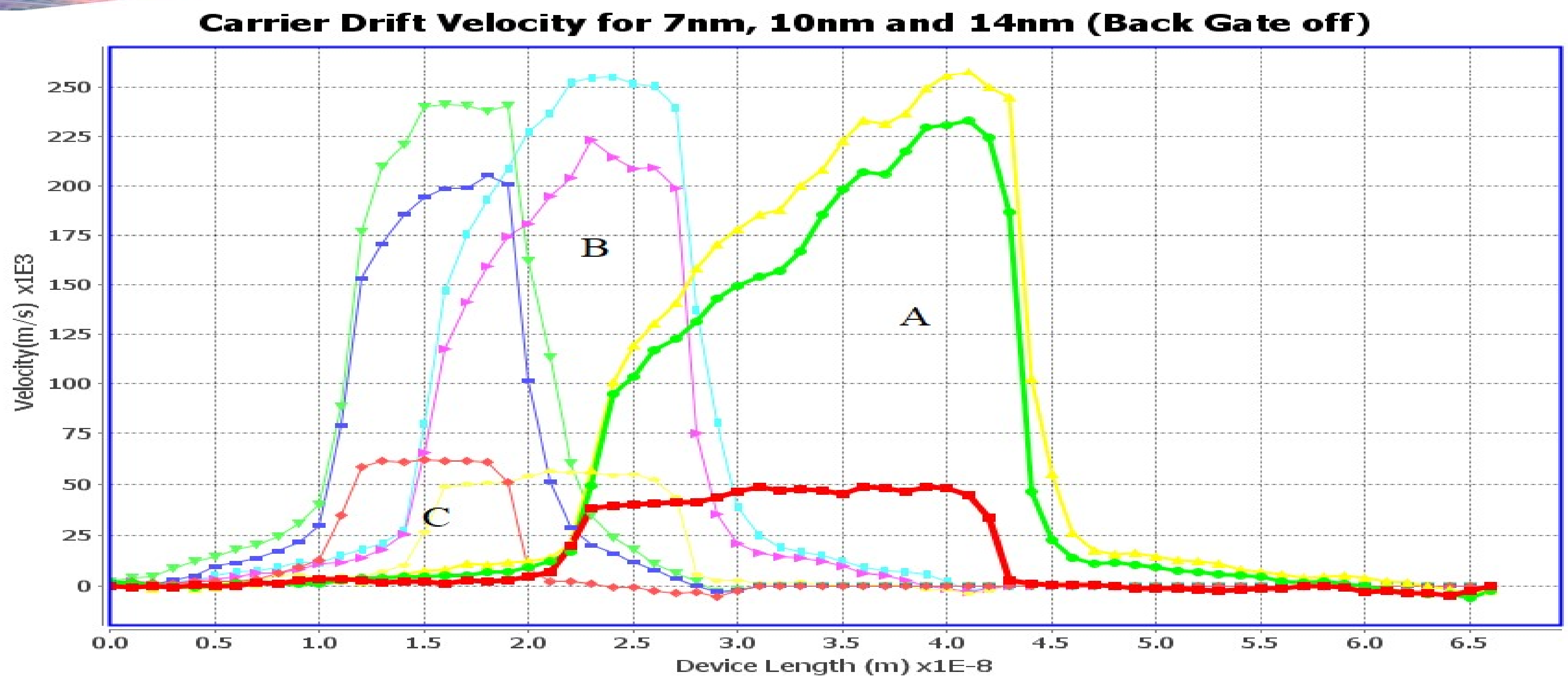
- Intervalley,
- Acoustic and
- Coulomb





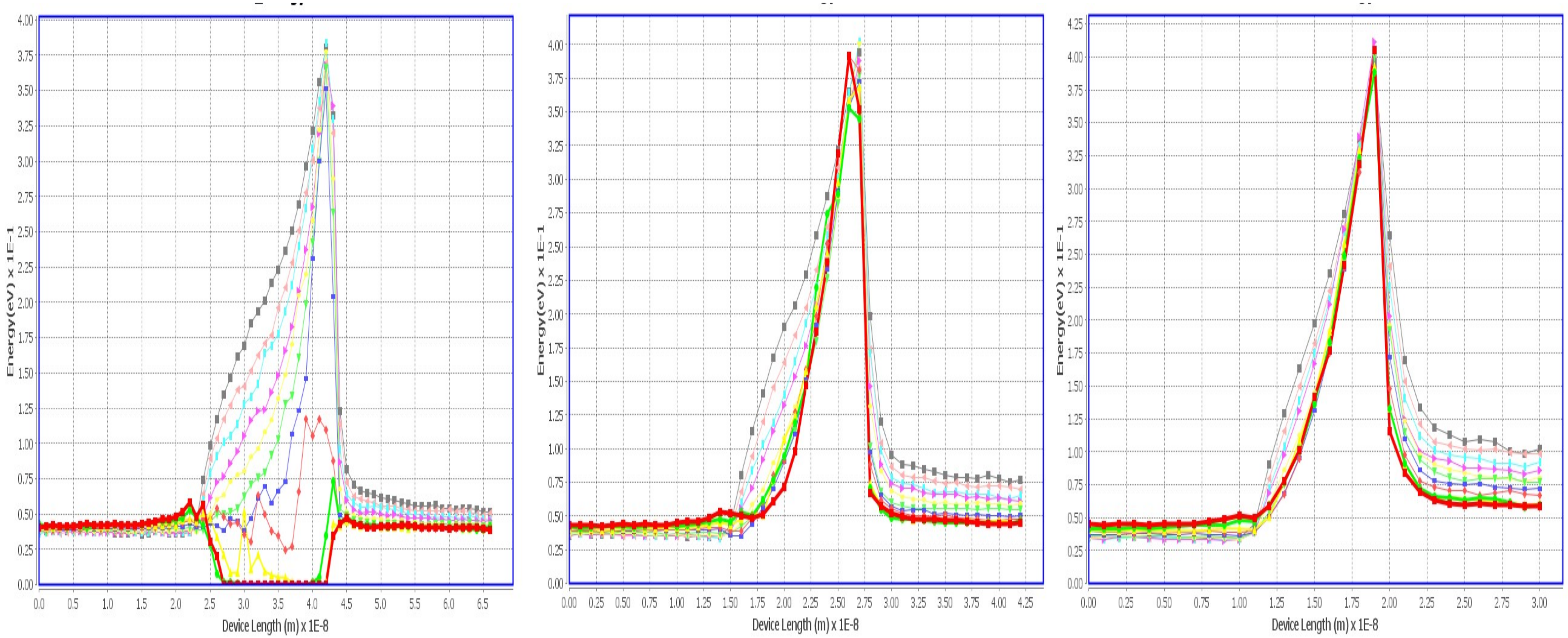
DRIFT VELOCITY





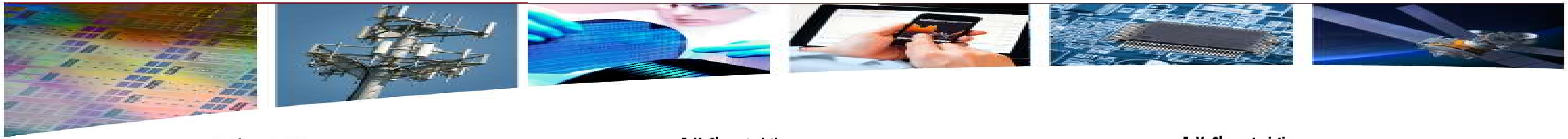
Carrier Drift velocity a) 14nm b) 10nm c) 7nm

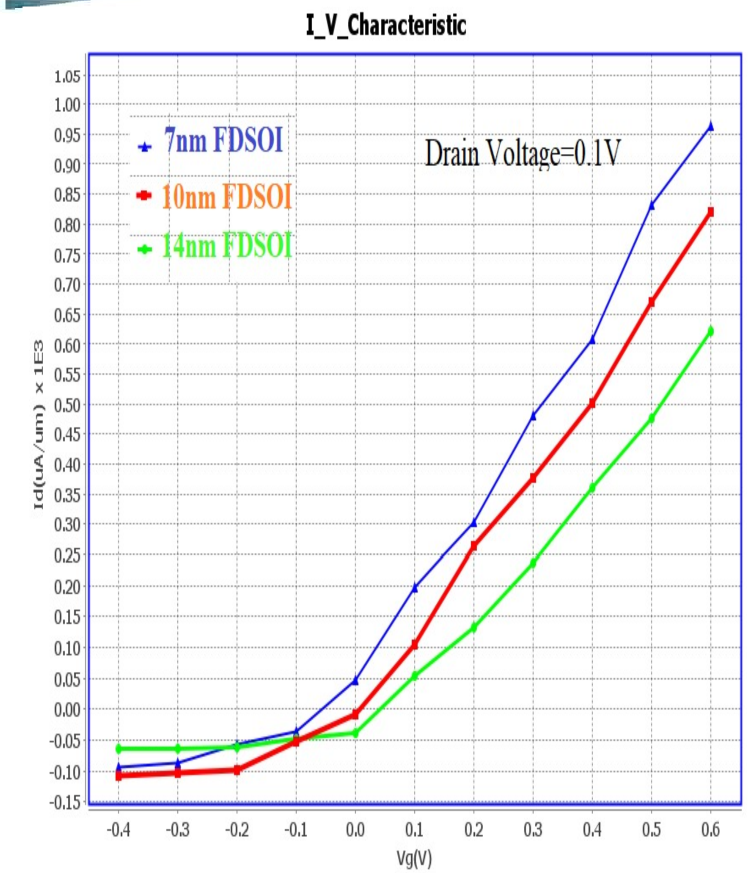
CARRIER AVERAGE ENERGY

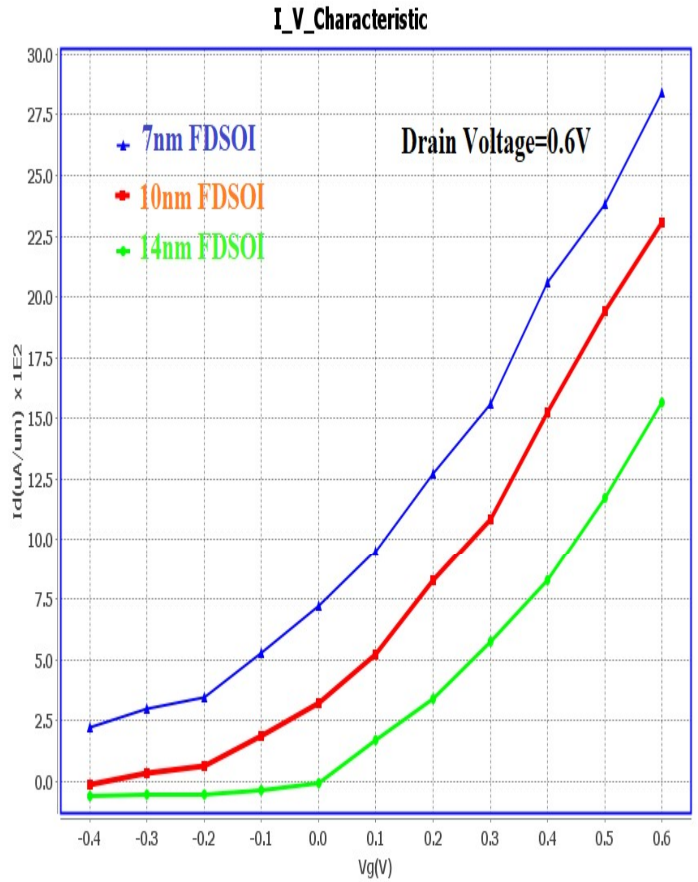


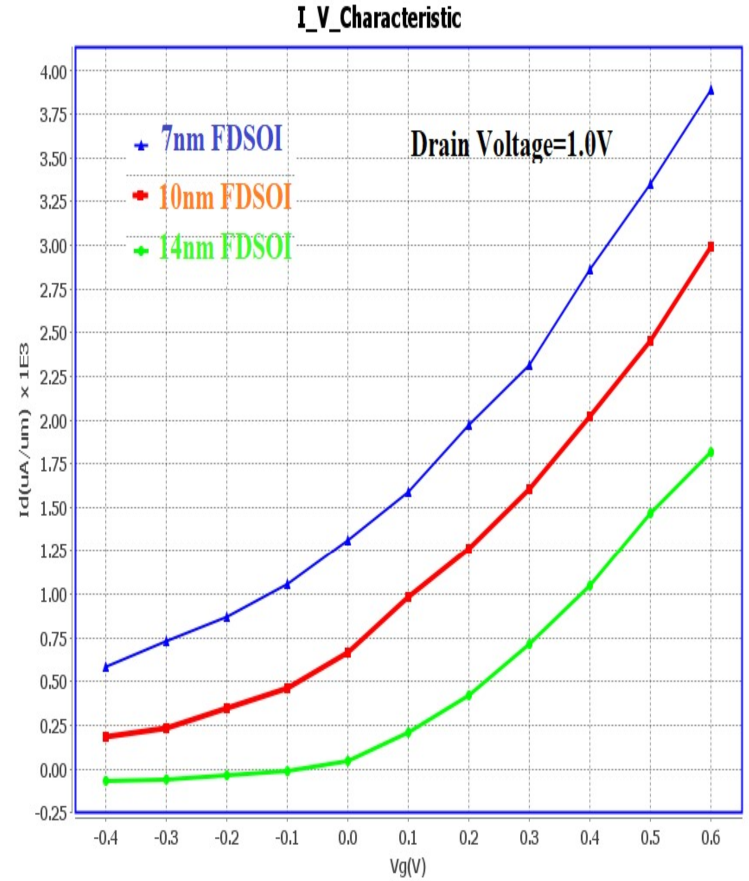
a) 14nm FDSOI MOSFET b) 10nm FDSOI MOSFET c) 7nm FDSOI MOSFET

Transfer I_d - V_g Characteristics

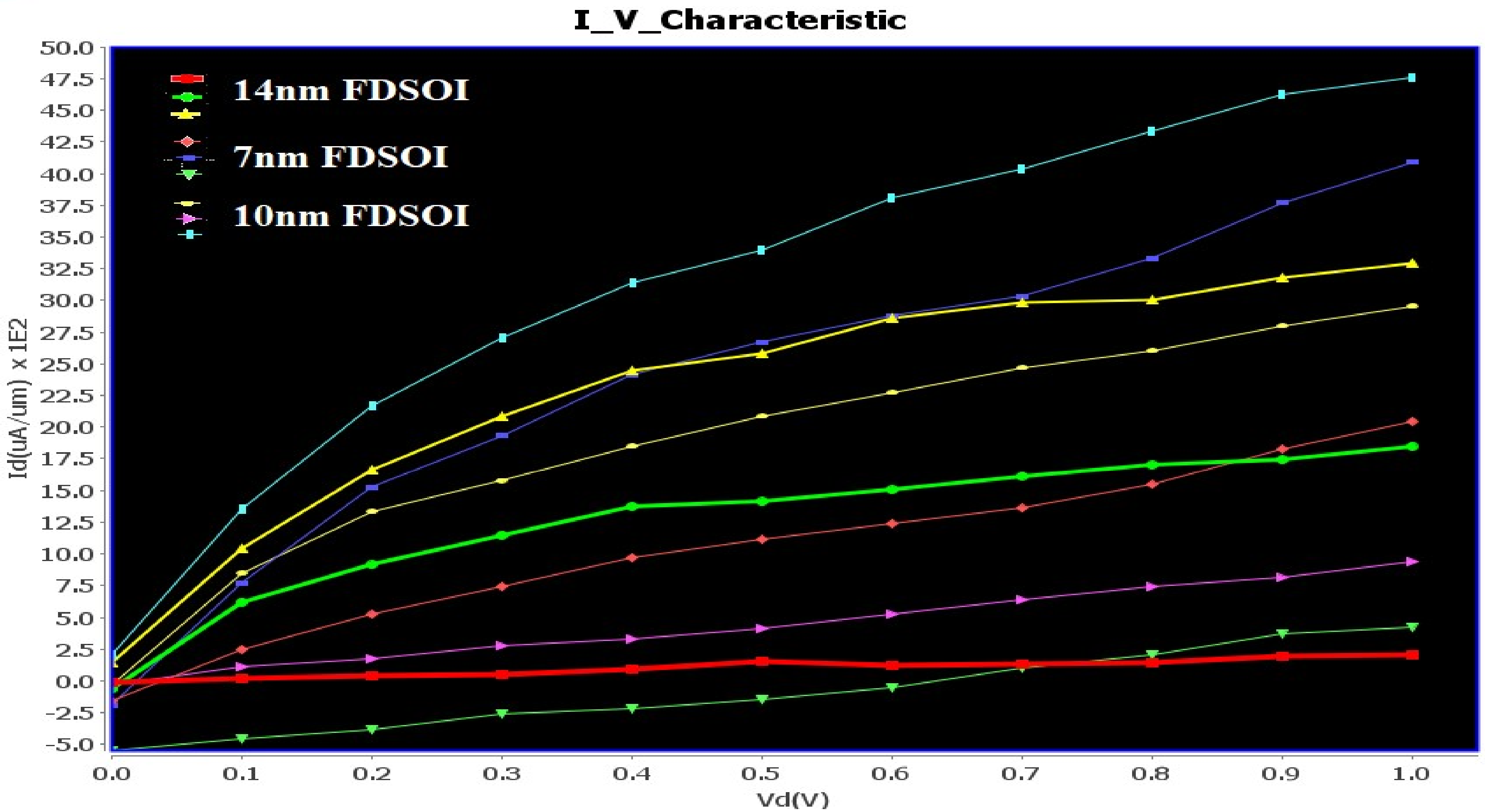




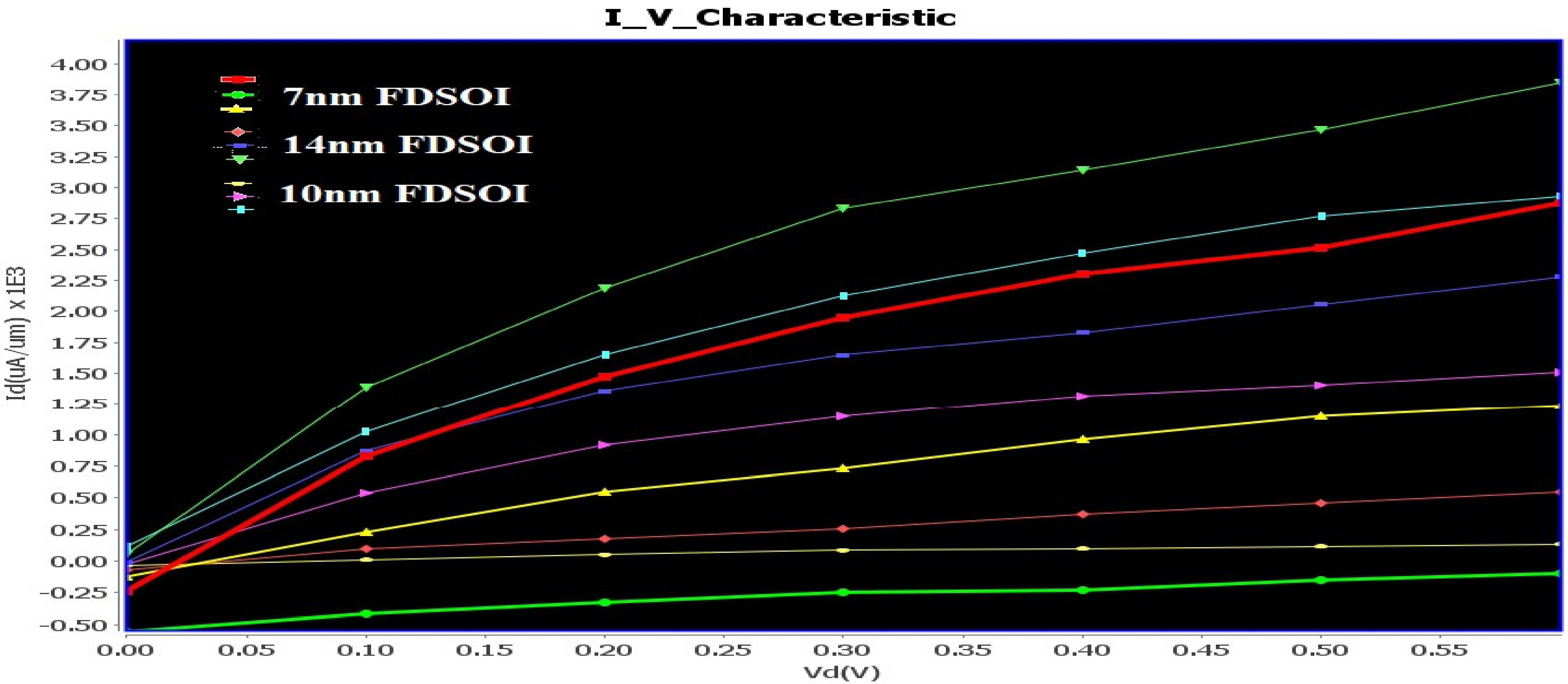




Single Gate I_d - V_d Characteristics



Dual Gate I_d - V_d Characteristics



Thank You

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